

Power Transistors



E-pack

Bipolar transistors

Type No.	Absolute Maximum Ratings								Electrical Characteristics								Outline		
EIAJ No.	V _{CE0} [V]	V _{CE0} [V]	V _{EB0} [V]	I _C [A]	I _B [A]	P _T [W]	T _{stg} [°C]	T _J [°C]	V _{CE0} (sus) (min) [V]	h _{FE} (min)	V _{CE} (sat) (max) [V]	V _{BE} (sat) (max) [V]	θ _{jc} (max) [°C/W]	f _T (typ) [MHz]	t _{on} (max) [μs]	t _s (max) [μs]			t _f (max) [μs]
2SA1795	−60	−40	−7	−5	−1.5	10	−55	150	−40	70	−0.3	−1.2	12.5	50	0.3	1.5	0.5	E-pack	79-3
1796				−7															
1876				−3	−1														
1877	−80	−80		−5	−1.5		150		−80								0.2		
2SC4668	60	40	7	7	1.5	10	−55	150	40	70	0.3	1.2	12.5	50	0.3	1.5	0.5	E-pack	79-3
4669				10															
4978				3	1														
4979	100	80		5	1.5		150		80								0.2		

Power MOSFET



B-pack



E-pack



STO-220

N-Channel, Enhancement type

Type No.	Absolute Maximum Ratings					Electrical Characteristics					Outline	
EIAJ No.	Tch [°C]	V _{DS} [V]	V _{GS} [V]	I _D [A]	P _T [W]	R _{DS(ON)} (max) [Ω]	C _{iss} (typ) [pF]	C _{rss} (typ) [pF]	t _{on} (typ) [ns]	t _{off} (typ) [ns]		
2SK1861	150	150	±20	4	10	0.6	480	50	57	121	E-pack	79-4
1931		200	±30	5	20	0.65	360	45	55	75		
1194		230	±20	0.5	6	8	45	4.5	30	50		
★F05B23VR				0.5	1.5	8	45	4.5	30	50	B-pack	75
1195				1.5	10	2	160	20	37	50		
2177		500	±30	1	10	7	140	13	35	60	E-pack	79-4
2178				2	15	4	220	17	40	70		
2179				3	20	2.3	400	30	45	90		
☆ 2663				900	1	10	14	230	5	10		
2SK2489		150	180	±30	10	45	0.25	720	80	50	140	STO-220
2491	20				70	0.13	1600	190	95	300		
2062	250		10		50	0.5	675	85	75	100		
2063			20		65	0.25	1200	155	140	160		
2064	300		10		50	0.7	700	85	75	100		
2065			20		65	0.35	1300	155	140	160		
2181	500		3		40	2.3	400	30	45	90		
2184			5		50	1.5	580	45	55	110		
2187			10		60	1.0	890	70	70	140		
2191			12		60	0.7	1200	90	90	190		
☆ 2665	900		3		50	4.7	630	16	40	140		
☆ 2670			5		60	2.8	1140	23	55	210		

☆ : New products

★ : Under development